

RS1AF THRU RS1MF

SMAF Plastic-Encapsulate Diodes

Fast Recovery Rectifier

Features

- •lo
- •VRRM 50V-1000V
- High surge current capability

1A

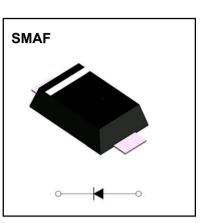
- •Glass passivated chip
- Polarity: Color band denotes cathode

Applications

Rectifier

Marking

• RS1AF-RS1MF : RS1A-RS1M



Limiting Values (Absolute Maximum Rating)

ltow	Symbo	nit	Conditions	RS1							
Item			Conditions	AF	BF	DF	GF	JF	KF	MF	
Repetitive Peak Reverse Voltage	V _{RRM}	V		50	100	200	400	600	800	1000	
Maximum RMS Voltage	V _{RMS}	V		35	70	140	280	420	560	700	
Average Forward Current	$I_{F(AV)}$	A	0Hz Half-sine wave, Resistance oad, Ta=90 $^\circ\!\!\!\mathrm{C}$	1							
Surge(Non-repetitive)Forward Current	I _{FSM}	A	60Hz Half-sine wave,1 cyde, a=25℃	30							
Junction Temperature	TJ	°C		-55 ~ +150							
Storage Temperature	T _{STG}	°C		-55 ~ +150							

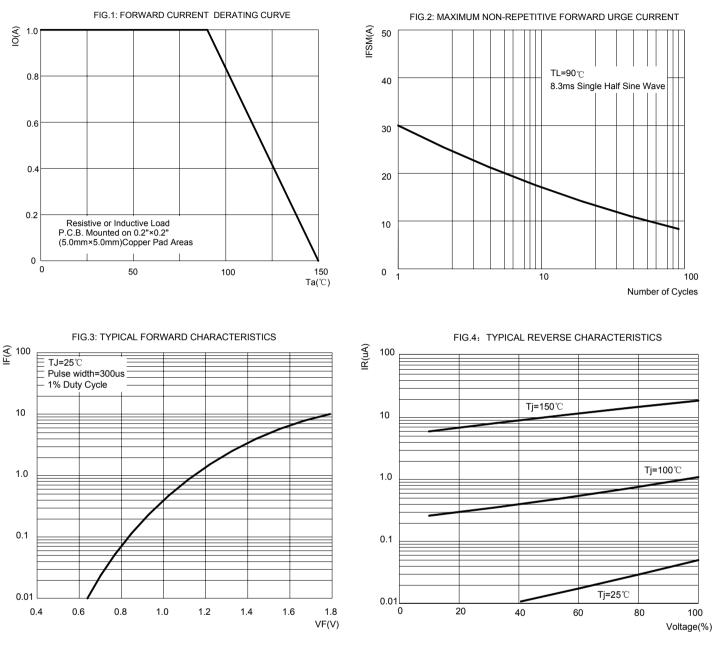
Electrical Characteristics (Ta 25°C Unless otherwise specified)

			Test Condition		RS1						
ltem	Symbol	Unit			AF	BF	DF	GF	JF	KF	MF
Peak Forward Voltage	$V_{\sf FM}$	V	I _{FM} =1.0A		1.3						
	RRM1		<u> </u>	T _a =25℃	5						
Peak Reverse Current	RRM2	μΑ	V _{RM} =V _{RRM}	T _a =125℃				50			
Reverse Recovery time	t _{rr}	ns	I _F =0.5A I _R =1A I _{RR} =0.25A			150			250	50 500	
Thermal	$R_{_{ heta_{J}-A}}$	°C/W	Between jun	ction and ambient	105 ¹⁾						
Resistance(Typical)	R _{θJ-L}	0700	Between junction and terminal		32 ¹⁾						

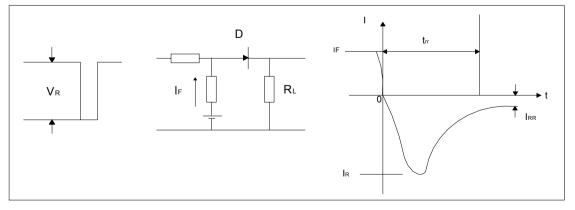
Notes:

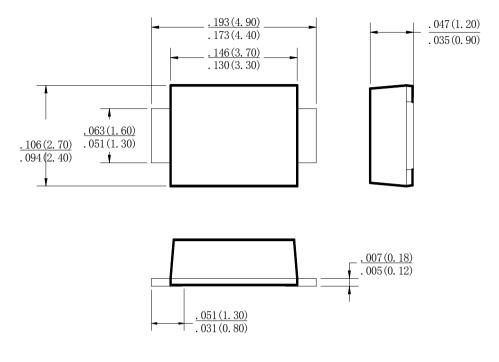
Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas

Typical Characteristics



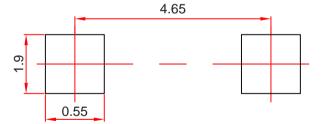






Dimensions in inches and (millimeters)

SMAF Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

NOTICE

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High Diode Semiconductor

Reel Taping Specifications For Surface Mount Devices- SMAF

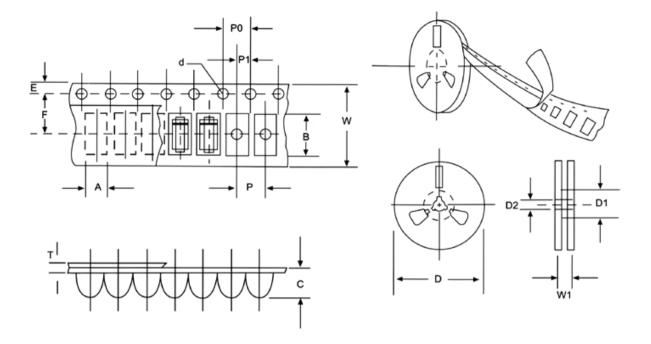


FIG:CONFIGURATION OF AXIAL TAPING

ITEM	SYMBOL	SMAF mm(inch)	
Carrier width	А	2.83+0.1(0.112+0.004)	
Carrier length	В	4.90+0.1(0.193+0.004)	
Carrier depth	С	1.45+0.1(0.057+0.004)	
Sprocket hole	d	1.55+0.05(0.061+0.002)	
Reel outside diameter	D	280/178+2.0(11/7.0+0.079)	
Reel inner diameter	D1	8.0+0.2(0.315+0.008)	
Feed hole diameter	D2	13+0.5(0.512+0.020)	
Strocket hole position	E	1.75+0.1(0.069+0.004)	
Punch hole position	F	5.5+0.05(0.217+0.002)	
Punch hole pitch	Р	4.0+0.1(0.157+0.004)	
Sprocket hole pitch	P0	4.0+0.1(0.157+0.004)	
Embossment center	P1	2.0+0.1(0.079+0.004)	
Totall tape thickness	Т	0.23-0.29(0.009-0.011)	
Tape width	W	12.0+0.1(0.472+0.004)	
Reel width	W1	16.8+2.0(0.661+0.079)	

NOTE: Devices are packde in accordance with EIA standard RS-481-A and specification given above.

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